

## Features

- AEC-Q100 qualified
- Temperature ranges
  - Automotive-E: -40 °C to +125 °C
- High speed
  - $t_{AA} = 10$  ns
- Low active and standby currents
  - $I_{CC} = 90$  mA typical
  - $I_{SB2} = 20$  mA typical
- 1.0 V data retention
- Automatic power-down when deselected
- Transistor-transistor logic (TTL)-compatible inputs and outputs
- Easy memory expansion with  $\overline{CE}$  and  $\overline{OE}$  features
- Available in Pb-free 48-ball very fine-pitch ball grid array (VFBGA) package

## Functional Description

The CY7C1051H<sup>[1]</sup> is a high-performance CMOS fast static RAM automotive part with embedded ECC.

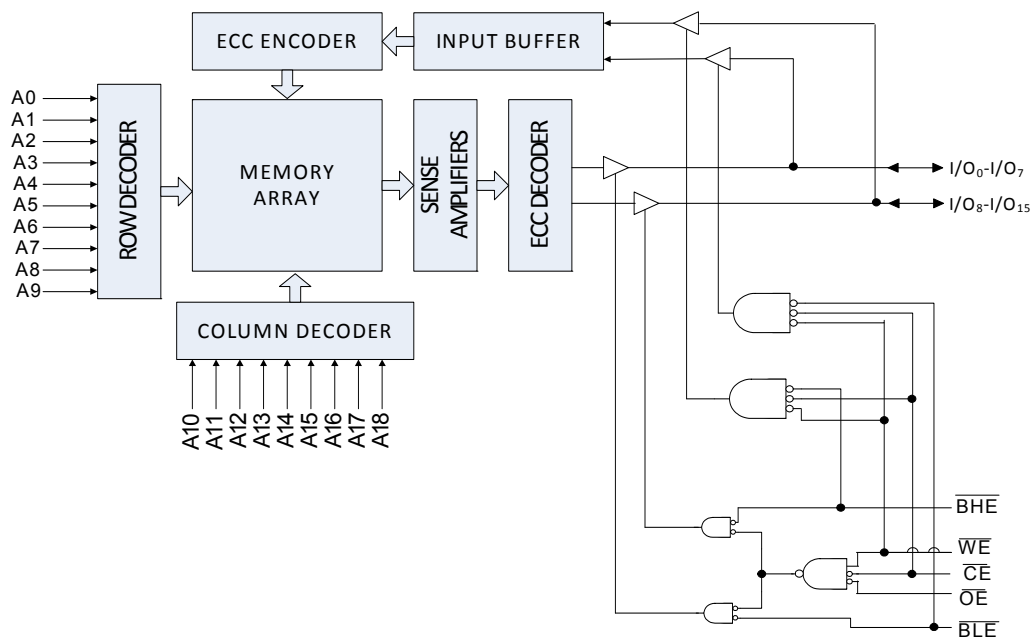
To write to the device, take Chip Enable ( $\overline{CE}$ ) and Write Enable ( $\overline{WE}$ ) inputs LOW. If Byte LOW Enable ( $\overline{BLE}$ ) is LOW, then data from I/O pins ( $I/O_0$ – $I/O_7$ ), is written into the location specified on the address pins ( $A_0$ – $A_{18}$ ). If Byte HIGH Enable ( $\overline{BHE}$ ) is LOW, then data from I/O pins ( $I/O_8$ – $I/O_{15}$ ) is written into the location specified on the address pins ( $A_0$ – $A_{18}$ ).

To read from the device, take Chip Enable ( $\overline{CE}$ ) and Output Enable ( $\overline{OE}$ ) LOW while forcing the Write Enable ( $\overline{WE}$ ) HIGH. If Byte LOW Enable ( $\overline{BLE}$ ) is LOW, then data from the memory location specified by the address pins appears on  $I/O_0$ – $I/O_7$ . If Byte HIGH Enable ( $\overline{BHE}$ ) is LOW, then data from memory appears on  $I/O_8$  to  $I/O_{15}$ . See the [Truth Table on page 11](#) for a complete description of read and write modes.

The input/output pins ( $I/O_0$ – $I/O_{15}$ ) are placed in a high-impedance state when the device is deselected ( $\overline{CE}$  HIGH), the outputs are disabled ( $\overline{OE}$  HIGH), the  $\overline{BHE}$  and  $\overline{BLE}$  are disabled ( $\overline{BHE}$ ,  $\overline{BLE}$  HIGH), or a write operation ( $\overline{CE}$  LOW, and  $\overline{WE}$  LOW) is in progress.

The CY7C1051H is available in 48-ball VFBGA package.

## Logic Block Diagram – CY7C1051H



### Note

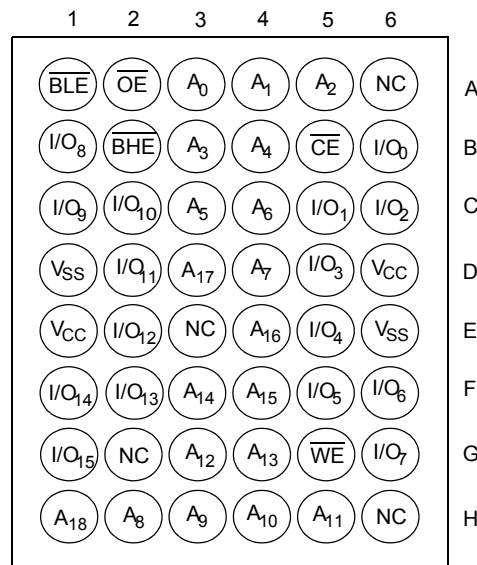
1. This device does not support automatic write-back on error detection.

**Contents**

<b>Pin Configurations</b> .....	<b>3</b>	<b>Ordering Information</b> .....	<b>12</b>
<b>Product Portfolio</b> .....	<b>3</b>	Ordering Code Definitions .....	12
<b>Maximum Ratings</b> .....	<b>4</b>	<b>Package Diagram</b> .....	<b>13</b>
<b>Operating Range</b> .....	<b>4</b>	<b>Acronyms</b> .....	<b>14</b>
<b>DC Electrical Characteristics</b> .....	<b>4</b>	<b>Document Conventions</b> .....	<b>14</b>
<b>Capacitance</b> .....	<b>5</b>	Units of Measure .....	14
<b>Thermal Resistance</b> .....	<b>5</b>	<b>Document History Page</b> .....	<b>15</b>
<b>AC Test Loads and Waveforms</b> .....	<b>5</b>	<b>Sales, Solutions, and Legal Information</b> .....	<b>16</b>
<b>Data Retention Characteristics</b> .....	<b>6</b>	Worldwide Sales and Design Support .....	16
<b>Data Retention Waveform</b> .....	<b>6</b>	Products .....	16
<b>AC Switching Characteristics</b> .....	<b>7</b>	PSoC@Solutions .....	16
<b>Switching Waveforms</b> .....	<b>8</b>	Cypress Developer Community .....	16
<b>Truth Table</b> .....	<b>11</b>	Technical Support .....	16

## Pin Configurations

Figure 1. 48-ball FBGA pinout (Top View) <sup>[2]</sup>



## Product Portfolio

Product	Range	V <sub>CC</sub> Range (V)	Speed (ns)	Power Dissipation			
				Operating I <sub>CC</sub> , (mA)		Standby, I <sub>SB2</sub> (mA)	
				f = f <sub>max</sub>			
				Typ <sup>[3]</sup>	Max	Typ <sup>[3]</sup>	Max
CY7C1051H	Automotive-E	2.2 V–3.6 V	10	90	160	20	50

**Notes**

- NC pins are not connected on the die.
- Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V<sub>CC</sub> = 3 V (for V<sub>CC</sub> range of 2.2 V–3.6 V), T<sub>A</sub> = 25 °C.

## Maximum Ratings

Exceeding the maximum ratings may shorten the useful life of the device. These user guidelines are not tested.

Storage temperature	..... -65 °C to +150 °C
Ambient temperature with power applied	..... -55 °C to +125 °C
Supply voltage on V <sub>CC</sub> to relative GND [4]	..... -0.5 V to +4.6 V
DC voltage applied to outputs in high-Z state [4]	..... -0.3 V to V <sub>CC</sub> + 0.3 V

DC input voltage [4]	..... -0.3 V to V <sub>CC</sub> + 0.3 V
Current into outputs (LOW)	..... 20 mA
Static discharge voltage (per MIL-STD-883, Method 3015)	..... > 2001 V
Latch-up current	..... > 200 mA

## Operating Range

Range	Ambient Temperature	V <sub>CC</sub>
Automotive-E	-40 °C to +125 °C	2.2 V to 3.6 V

## DC Electrical Characteristics

Over the Operating Range

Parameter	Description	Test Conditions	Automotive-E		Unit		
			Min	Max			
V <sub>OH</sub>	Output HIGH voltage	2.2 V to 2.7 V	V <sub>CC</sub> = Min, I <sub>OH</sub> = -1.0 mA		2	-	V
		2.7 V to 3.0 V	V <sub>CC</sub> = Min, I <sub>OH</sub> = -4.0 mA		2.2	-	V
		3.0 V to 3.6 V	V <sub>CC</sub> = Min, I <sub>OH</sub> = -4.0 mA		2.4	-	V
V <sub>OL</sub>	Output LOW voltage	2.2 V to 2.7 V	V <sub>CC</sub> = Min, I <sub>OL</sub> = 2 mA		-	0.4	V
		2.7 V to 3.6 V	V <sub>CC</sub> = Min, I <sub>OL</sub> = 8 mA		-	0.4	V
V <sub>IH</sub>	Input HIGH voltage	2.2 V to 2.7 V	-		2	V <sub>CC</sub> + 0.3	V
		2.7 V to 3.6 V	-		2	V <sub>CC</sub> + 0.3	V
V <sub>IL</sub>	Input LOW voltage [4]	2.2 V to 2.7 V	-		-0.3	0.6	V
		2.7 V to 3.6 V	-		-0.3	0.8	V
I <sub>Ix</sub>	Input leakage current	GND ≤ V <sub>IN</sub> ≤ V <sub>CC</sub>		-5	+5	μA	
I <sub>OZ</sub>	Output leakage current	GND ≤ V <sub>OUT</sub> ≤ V <sub>CC</sub> , Output disabled		-5	+5	μA	
I <sub>CC</sub>	Operating supply current	V <sub>CC</sub> = Max, I <sub>OUT</sub> = 0 mA, CMOS levels	f = f <sub>MAX</sub> = 1/t <sub>RC</sub>	-	160	mA	
I <sub>SB1</sub>	Automatic CE power down current – TTL inputs	Max V <sub>CC</sub> , CE ≥ V <sub>IH</sub> , V <sub>IN</sub> ≥ V <sub>IH</sub> or V <sub>IN</sub> ≤ V <sub>IL</sub> , f = f <sub>MAX</sub>		-	60	mA	
I <sub>SB2</sub>	Automatic CE power down current – CMOS inputs	Max V <sub>CC</sub> , CE ≥ V <sub>CC</sub> - 0.2 V, V <sub>IN</sub> ≥ V <sub>CC</sub> - 0.2 V or V <sub>IN</sub> ≤ 0.2 V, f = 0		-	50	mA	

### Note

4. V<sub>IL(min)</sub> = -2.0 V and V<sub>IH(max)</sub> = V<sub>CC</sub> + 2 V for pulse durations of less than 20 ns.

### Capacitance

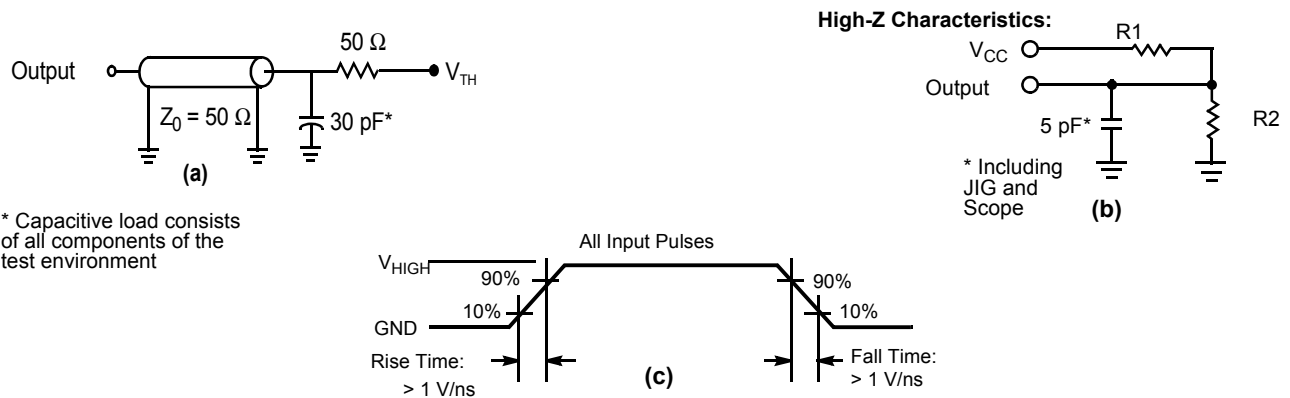
Parameter <sup>[5]</sup>	Description	Test Conditions	Max	Unit
C <sub>IN</sub>	Input capacitance	T <sub>A</sub> = 25 °C, f = 1 MHz, V <sub>CC</sub> = 3.3 V	10	pF
C <sub>OUT</sub>	I/O capacitance		10	pF

### Thermal Resistance

Parameter <sup>[5]</sup>	Description	Test Conditions	48-ball VFBGA Package	Unit
Θ <sub>JA</sub>	Thermal resistance (junction to ambient)	Still air, soldered on a 3 × 4.5 inch, four-layer printed circuit board	31.50	°C/W
Θ <sub>JC</sub>	Thermal resistance (junction to case)		15.75	°C/W

### AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms <sup>[6]</sup>



Parameters	3.0 V	Unit
R1	317	Ω
R2	351	Ω
V <sub>TH</sub>	1.5	V
V <sub>HIGH</sub>	3	V

**Notes**

5. Tested initially and after any design or process changes that may affect these parameters.
6. Full device AC operation assumes a 100-μs ramp time from 0 to V<sub>CC(min)</sub> and 100-μs wait time after V<sub>CC</sub> stabilization.

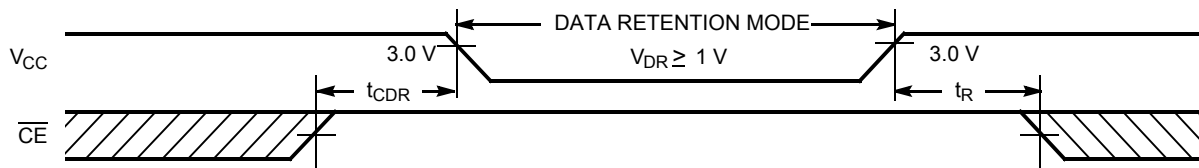
## Data Retention Characteristics

Over the Operating Range

Parameter	Description	Conditions	Min	Max	Unit
$V_{DR}$	$V_{CC}$ for data retention	–	1.0	–	V
$I_{CCDR}$	Data retention current	$V_{CC} = V_{DR}$ , $\overline{CE} \geq V_{CC} - 0.2$ V, $V_{IN} \geq V_{CC} - 0.2$ V or $V_{IN} \leq 0.2$ V	–	50	mA
$t_{CDR}^{[7]}$	Chip deselect to data retention time	–	0	–	ns
$t_R^{[8]}$	Operation recovery time	$V_{CC} \geq 2.2$ V	10	–	ns

## Data Retention Waveform

Figure 3. Data Retention Waveform



### Notes

7. Tested initially and after any design or process changes that may affect these parameters.
8. Full device operation requires linear  $V_{CC}$  ramp from  $V_{DR}$  to  $V_{CC(min.)} \geq 100 \mu s$  or stable at  $V_{CC(min.)} \geq 100 \mu s$ .

## AC Switching Characteristics

Over the Operating Range

Parameter [9]	Description	-10		Unit
		Min	Max	
<b>Read Cycle</b>				
$t_{power}^{[10]}$	$V_{CC}$ (typical) to the First Access	100	–	μs
$t_{RC}$	Read Cycle Time	10	–	ns
$t_{AA}$	Address to Data Valid	–	10	ns
$t_{OHA}$	Data Hold from Address Change	3	–	ns
$t_{ACE}$	$\overline{CE}$ LOW to Data Valid	–	10	ns
$t_{DOE}$	$\overline{OE}$ LOW to Data Valid	–	5	ns
$t_{LZOE}$	$\overline{OE}$ LOW to Low Z [11]	0	–	ns
$t_{HZOE}$	$\overline{OE}$ HIGH to High Z [11, 12]	–	5	ns
$t_{LZCE}$	$\overline{CE}$ LOW to Low Z [11]	3	–	ns
$t_{HZCE}$	$\overline{CE}$ HIGH to High Z [11, 12]	–	5	ns
$t_{PU}$	$\overline{CE}$ LOW to Power Up [13]	0	–	ns
$t_{PD}$	$\overline{CE}$ HIGH to Power Down [13]	–	10	ns
$t_{DBE}$	Byte Enable to Data Valid	–	5	ns
$t_{LZBE}$	Byte Enable to Low Z [11]	0	–	ns
$t_{HZBE}$	Byte Disable to High Z [11, 12]	–	6	ns
<b>Write Cycle</b> [14, 15]				
$t_{WC}$	Write Cycle Time	10	–	ns
$t_{SCE}$	$\overline{CE}$ LOW to Write End	7	–	ns
$t_{AW}$	Address Setup to Write End	7	–	ns
$t_{HA}$	Address Hold from Write End	0	–	ns
$t_{SA}$	Address Setup to Write Start	0	–	ns
$t_{PWE}$	$\overline{WE}$ Pulse Width	7	–	ns
$t_{SD}$	Data Setup to Write End	5	–	ns
$t_{HD}$	Data Hold from Write End	0	–	ns
$t_{LZWE}$	$\overline{WE}$ HIGH to Low Z [11]	3	–	ns
$t_{HZWE}$	$\overline{WE}$ LOW to High Z [11, 12]	–	5	ns
$t_{BW}$	Byte Enable to End of Write	7	–	ns

### Notes

9. Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5 V, input pulse levels of 0 to 3.0 V.
10.  $t_{POWER}$  gives the minimum amount of time that the power supply must be at typical  $V_{CC}$  values until the first memory access can be performed.
11. At any temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ ,  $t_{HZOE}$  is less than  $t_{LZOE}$ ,  $t_{HZBE}$  is less than  $t_{LZBE}$ , and  $t_{HZWE}$  is less than  $t_{LZWE}$  for any device.
12.  $t_{HZOE}$ ,  $t_{HZCE}$ ,  $t_{HZBE}$  and  $t_{HZWE}$  are specified with a load capacitance of 5 pF as in part (d) of Figure 2 on page 5. Transition is measured when the outputs enter a high impedance state.
13. These parameters are guaranteed by design and are not tested.
14. The internal write time of the memory is defined by the overlap of  $\overline{CE}$  LOW, and  $\overline{WE}$  LOW.  $\overline{CE}$  and  $\overline{WE}$  must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data setup and hold timing must refer to the leading edge of the signal that terminates the write.
15. The minimum write cycle time for Write Cycle No. 3 (WE Controlled, OE LOW) is the sum of  $t_{HZWE}$  and  $t_{SD}$ .

Switching Waveforms

Figure 4. Read Cycle No. 1 [16, 17]

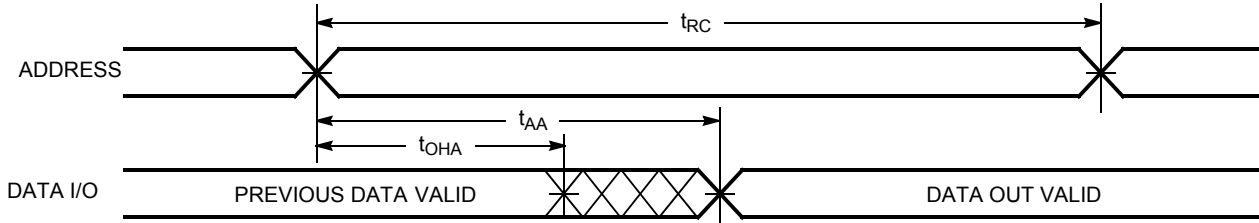
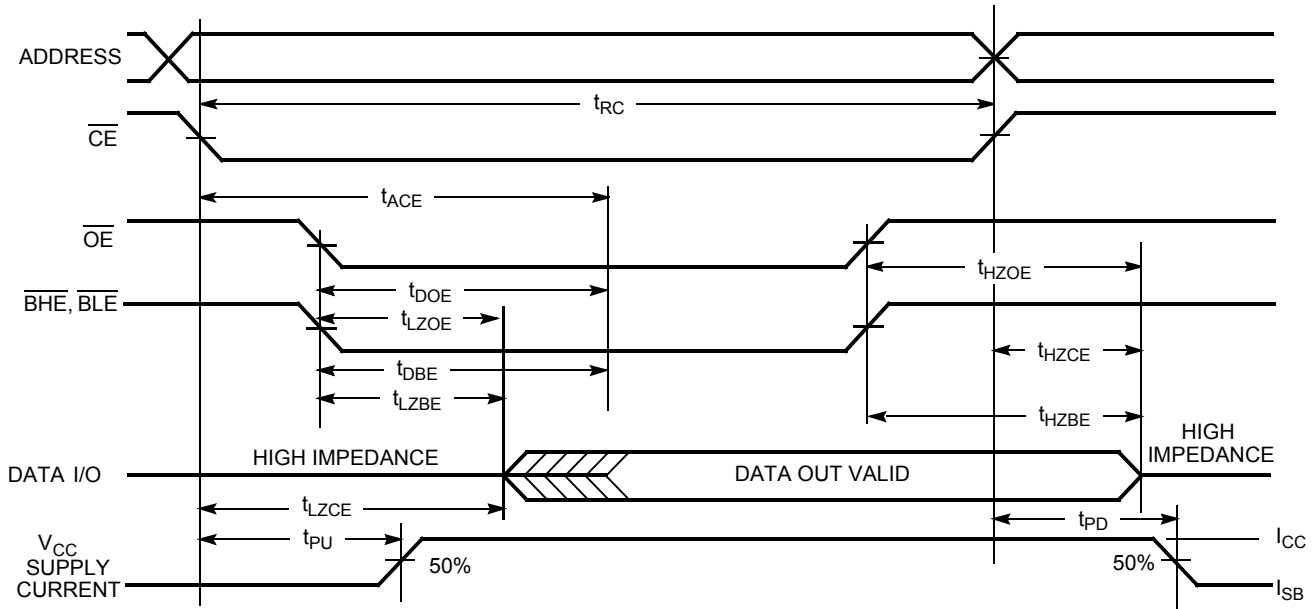


Figure 5. Read Cycle No. 2 ( $\overline{OE}$  Controlled) [17, 18]



Notes

- 16. Device is continuously selected.  $\overline{OE}$ ,  $\overline{CE} = V_{IL}$ ,  $\overline{BHE}$ ,  $\overline{BLE}$ , or both =  $V_{IL}$ .
- 17. WE is HIGH for Read cycle.
- 18. Address valid before or coincident with  $\overline{CE}$  transition LOW.



Switching Waveforms(continued)

Figure 6. Write Cycle No. 1 ( $\overline{\text{CE}}$  Controlled) [19, 20, 21]

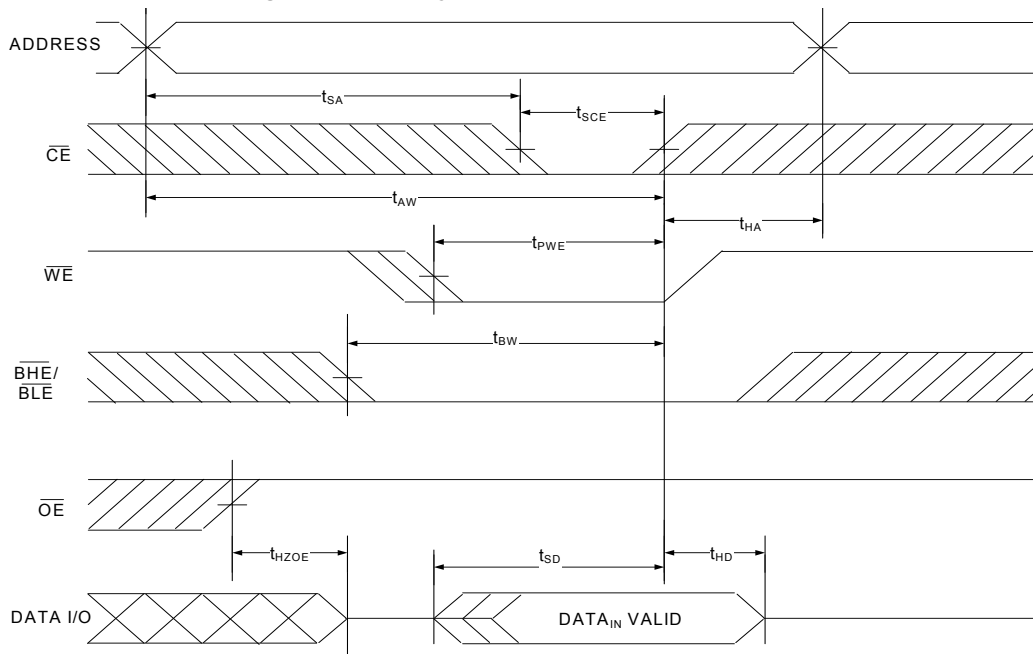
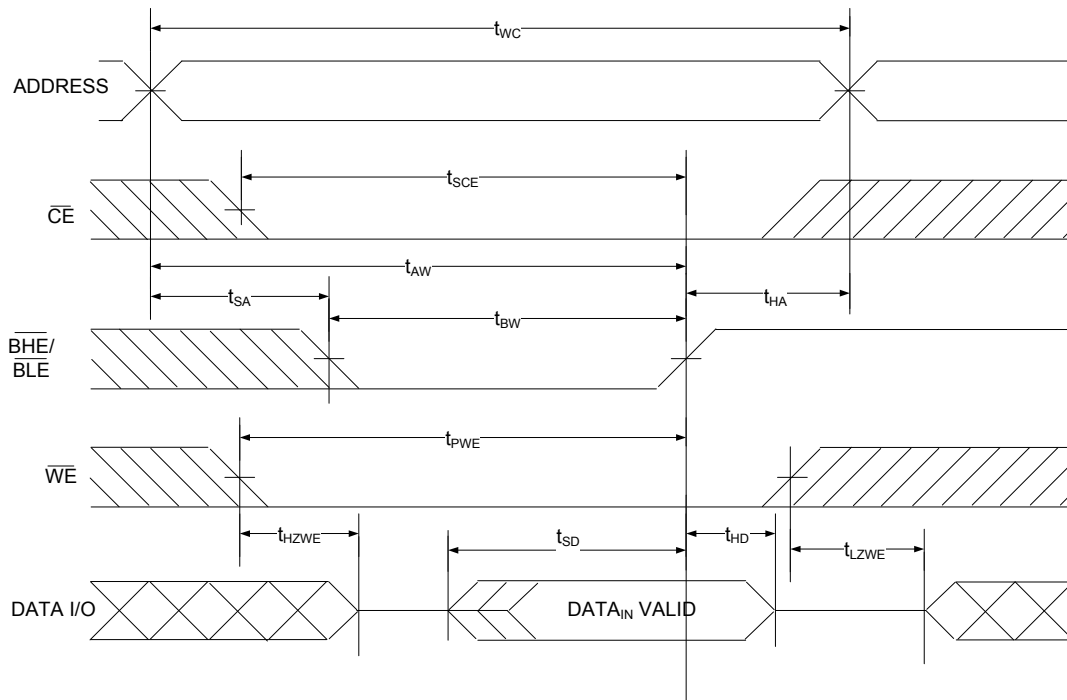


Figure 7. Write Cycle No. 2 ( $\overline{\text{BLE}}$  or  $\overline{\text{BHE}}$  Controlled) [19, 20, 21]



Notes

- 19. The internal write time of the memory is defined by the overlap of  $\overline{\text{WE}} = V_{\text{IL}}$ ,  $\overline{\text{CE}} = V_{\text{IL}}$ , and  $\overline{\text{BHE}}$  or  $\overline{\text{BLE}} = V_{\text{IL}}$ . These signals must be LOW to initiate a write and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.
- 20. Data I/O is in high-impedance state if  $\overline{\text{CE}} = V_{\text{IH}}$ , or  $\overline{\text{OE}} = V_{\text{IH}}$  or  $\overline{\text{BHE}}$ , and/or  $\overline{\text{BLE}} = V_{\text{IH}}$ .
- 21. During this period, the I/Os are in output state. Do not apply input signals.

Switching Waveforms(continued)

Figure 8. Write Cycle No. 3 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW) [22, 23, 24, 25]

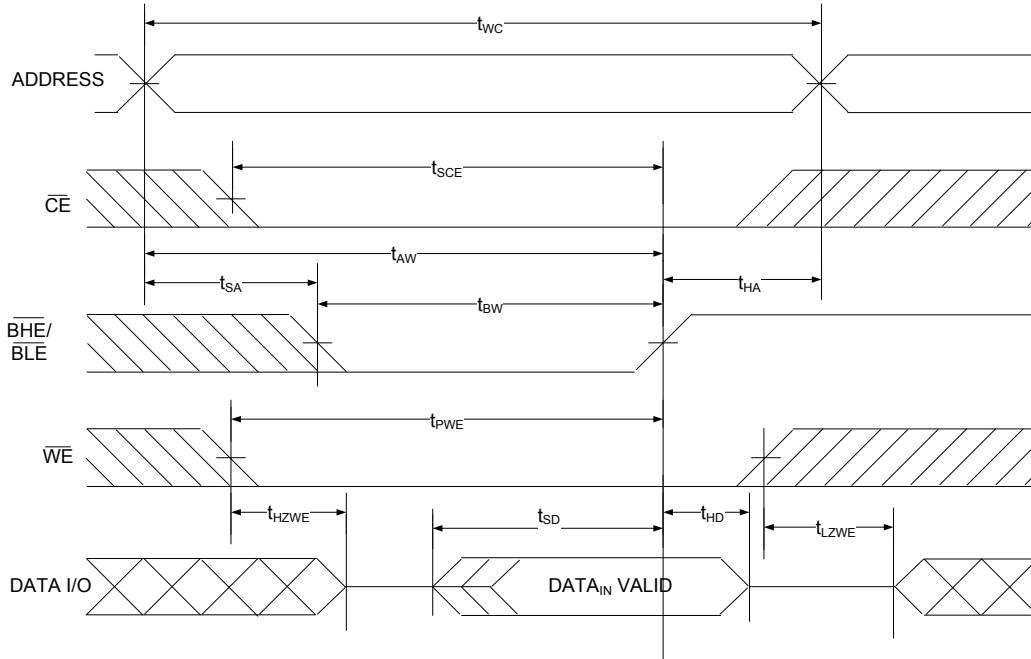
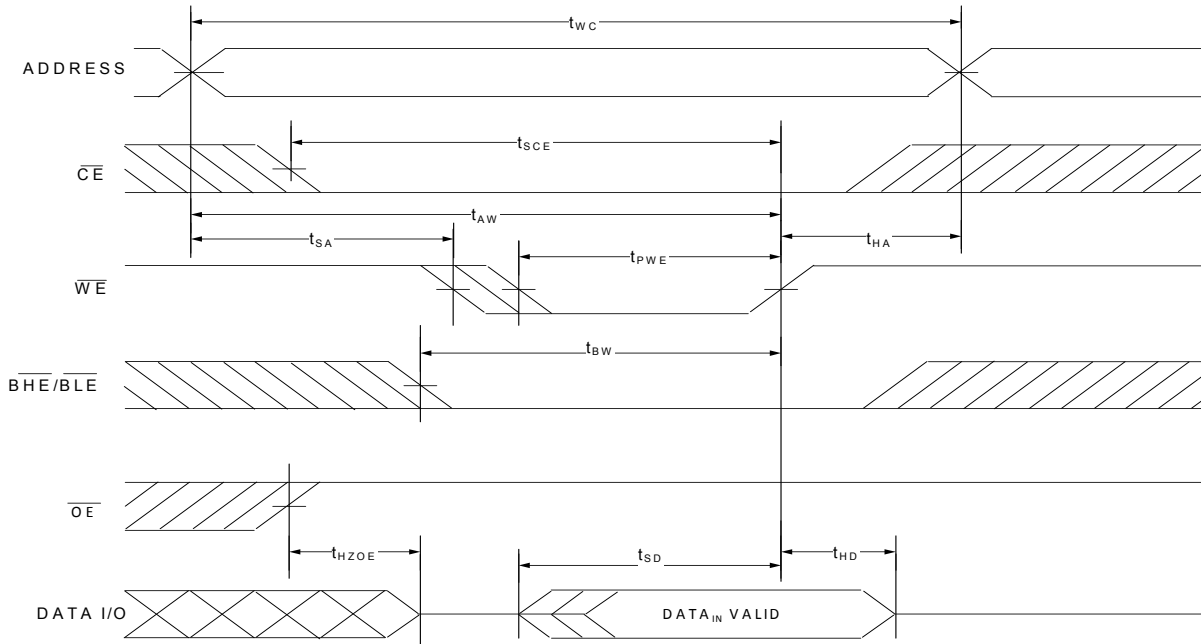


Figure 9. Write Cycle No. 4 ( $\overline{WE}$  Controlled) [23, 24]



Notes

- 22. The minimum write pulse width for Write Cycle No. 3 ( $\overline{WE}$  Controlled,  $\overline{OE}$  LOW) should be sum of  $t_{HZWE}$  and  $t_{SD}$ .
- 23. The internal write time of the memory is defined by the overlap of  $\overline{WE} = V_{IL}$ ,  $\overline{CE} = V_{IL}$ , and  $BHE$  or  $BLE = V_{IL}$ . These signals must be LOW to initiate a write, and the HIGH transition of any of these signals can terminate the operation. The input data setup and hold timing should be referenced to the edge of the signal that terminates the write.
- 24. Data I/O is in high impedance state if  $\overline{CE} = V_{IH}$ , or  $\overline{OE} = V_{IH}$  or  $\overline{BHE}$ , and/or  $\overline{BLE} = V_{IH}$ .
- 25. During this period the I/Os are in output state. Do not apply input signals.

## Truth Table

The truth table is as follows <sup>[26]</sup>:

$\overline{CE}$	$\overline{OE}$	$\overline{WE}$	BLE	BHE	I/O <sub>0</sub> -I/O <sub>7</sub>	I/O <sub>8</sub> -I/O <sub>15</sub>	Mode	Power
H	X	X	X	X	High-Z	High-Z	Power Down	Standby (I <sub>SB</sub> )
L	L	H	L	L	Data Out	Data Out	Read All Bits	Active (I <sub>CC</sub> )
L	L	H	L	H	Data Out	High-Z	Read Lower Bits Only	Active (I <sub>CC</sub> )
L	L	H	H	L	High-Z	Data Out	Read Upper Bits Only	Active (I <sub>CC</sub> )
L	X	L	L	L	Data In	Data In	Write All Bits	Active (I <sub>CC</sub> )
L	X	L	L	H	Data In	High-Z	Write Lower Bits Only	Active (I <sub>CC</sub> )
L	X	L	H	L	High-Z	Data In	Write Upper Bits Only	Active (I <sub>CC</sub> )
L	H	H	X	X	High-Z	High-Z	Selected, Outputs Disabled	Active (I <sub>CC</sub> )

**Note**

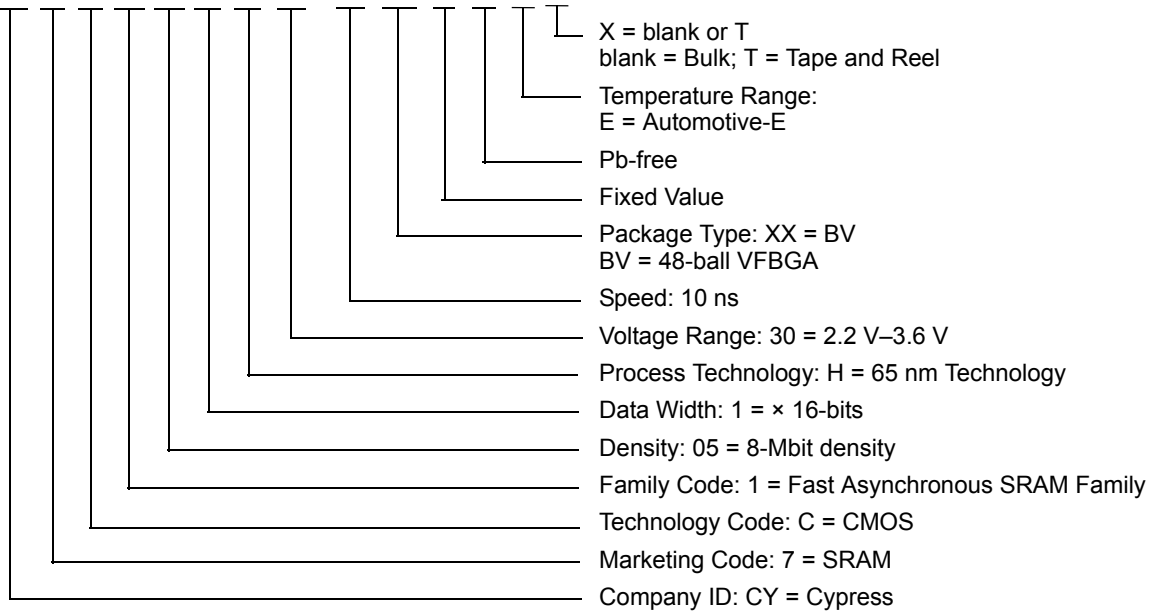
26. The input voltage levels on signals with value X should be either at V<sub>IH</sub> or V<sub>IL</sub>.

**Ordering Information**

Speed (ns)	Voltage Range	Ordering Code	Package Diagram	Package Type	Operating Range
10	2.2 V–3.6 V	CY7C1051H30-10BV1XE	51-85150	48-ball VFBGA (6 × 8 × 1.0 mm) (Pb-free)	Automotive-E
		CY7C1051H30-10BV1XET			

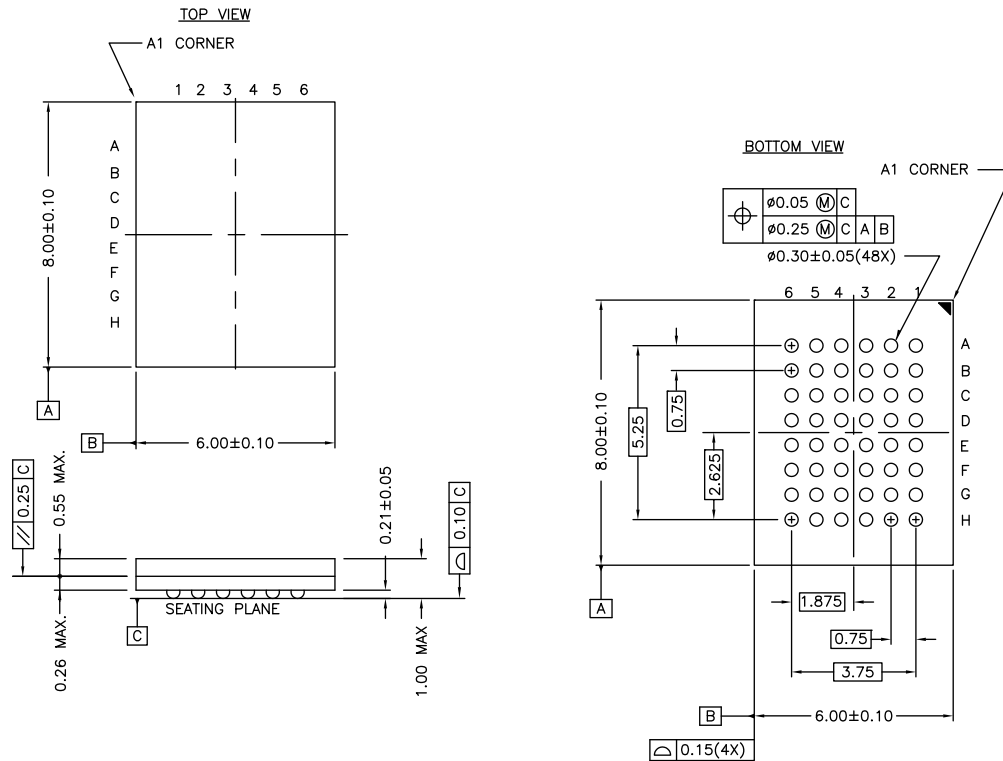
**Ordering Code Definitions**

CY 7 C 1 05 1 H 30 - 10 BV 1 X E X



**Package Diagram**

**Figure 10. 48-ball VFBGA (6 × 8 × 1.0 mm) BV48/BZ48 Package Outline, 51-85150**



NOTE:  
 PACKAGE WEIGHT: See Cypress Package Material Declaration Datasheet (PMDD) posted on the Cypress web.

51-85150 \*H

## Acronyms

**Table 1. Acronyms Used in this Document**

Acronym	Description
BHE	Byte High Enable
BLE	Byte Low Enable
CE	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
OE	Output Enable
SRAM	Static Random Access Memory
TTL	Transistor-Transistor Logic
VFBGA	Very Fine-Pitch Ball Grid Array
WE	Write Enable

## Document Conventions

### Units of Measure

**Table 2. Units of Measure**

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microampere
μs	microsecond
mA	milliampere
mm	millimeter
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt
W	watt

## Document History Page

Document Title: CY7C1051H Automotive, 8-Mbit (512K × 16) Static RAM Document Number: 001-87624				
Revision	ECN	Orig. of Change	Submission Date	Description of Change
*C	4961297	NILE	10/13/2015	Changed status from Preliminary to Final.
*D	5303970	VINI	06/10/2016	Added Automotive-A Temperature Range related information in all instances across the document. Added 44-pin TSOP II Package related information in all instances across the document. Updated <a href="#">Ordering Information</a> : Updated part numbers. Updated <a href="#">Package Diagram</a> : Added spec 51-85087 *E. Updated to new template. Completing Sunset Review.
*E	5333780	VINI	07/20/2016	Removed Automotive-A Temperature Range related information in all instances across the document. Removed 44-pin TSOP II Package related information in all instances across the document. Updated <a href="#">Features</a> : Added "AEC-Q100 qualified". Updated <a href="#">Ordering Information</a> : Updated part numbers. Updated <a href="#">Package Diagram</a> : Removed spec 51-85087 *E.
*F	5435305	VINI	09/13/2016	Updated <a href="#">Maximum Ratings</a> : Updated Note 4 (Replaced "2 ns" with "20 ns"). Updated <a href="#">DC Electrical Characteristics</a> : Removed Operating Range "2.7 V to 3.6 V" and all values corresponding to V <sub>OH</sub> parameter. Included Operating Ranges "2.7 V to 3.0 V" and "3.0 V to 3.6 V" and all values corresponding to V <sub>OH</sub> parameter. Updated <a href="#">Ordering Information</a> : Updated part numbers. Updated to new template.

## Sales, Solutions, and Legal Information

### Worldwide Sales and Design Support

Cypress maintains a worldwide network of offices, solution centers, manufacturer's representatives, and distributors. To find the office closest to you, visit us at [Cypress Locations](#).

#### Products

ARM® Cortex® Microcontrollers	<a href="http://cypress.com/arm">cypress.com/arm</a>
Automotive	<a href="http://cypress.com/automotive">cypress.com/automotive</a>
Clocks & Buffers	<a href="http://cypress.com/clocks">cypress.com/clocks</a>
Interface	<a href="http://cypress.com/interface">cypress.com/interface</a>
Internet of Things	<a href="http://cypress.com/iot">cypress.com/iot</a>
Lighting & Power Control	<a href="http://cypress.com/powerpsoc">cypress.com/powerpsoc</a>
Memory	<a href="http://cypress.com/memory">cypress.com/memory</a>
PSoC	<a href="http://cypress.com/psoc">cypress.com/psoc</a>
Touch Sensing	<a href="http://cypress.com/touch">cypress.com/touch</a>
USB Controllers	<a href="http://cypress.com/usb">cypress.com/usb</a>
Wireless/RF	<a href="http://cypress.com/wireless">cypress.com/wireless</a>

#### PSoC® Solutions

[PSoC 1](#) | [PSoC 3](#) | [PSoC 4](#) | [PSoC 5LP](#)

#### Cypress Developer Community

[Forums](#) | [Projects](#) | [Video](#) | [Blogs](#) | [Training](#) | [Components](#)

#### Technical Support

[cypress.com/support](http://cypress.com/support)

© Cypress Semiconductor Corporation, 2013-2016. This document is the property of Cypress Semiconductor Corporation and its subsidiaries, including Spansion LLC ("Cypress"). This document, including any software or firmware included or referenced in this document ("Software"), is owned by Cypress under the intellectual property laws and treaties of the United States and other countries worldwide. Cypress reserves all rights under such laws and treaties and does not, except as specifically stated in this paragraph, grant any license under its patents, copyrights, trademarks, or other intellectual property rights. If the Software is not accompanied by a license agreement and you do not otherwise have a written agreement with Cypress governing the use of the Software, then Cypress hereby grants you a personal, non-exclusive, nontransferable license (without the right to sublicense) (1) under its copyright rights in the Software (a) for Software provided in source code form, to modify and reproduce the Software solely for use with Cypress hardware products, only internally within your organization, and (b) to distribute the Software in binary code form externally to end users (either directly or indirectly through resellers and distributors), solely for use on Cypress hardware product units, and (2) under those claims of Cypress's patents that are infringed by the Software (as provided by Cypress, unmodified) to make, use, distribute, and import the Software solely for use with Cypress hardware products. Any other use, reproduction, modification, translation, or compilation of the Software is prohibited.

TO THE EXTENT PERMITTED BY APPLICABLE LAW, CYPRESS MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARD TO THIS DOCUMENT OR ANY SOFTWARE OR ACCOMPANYING HARDWARE, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE. To the extent permitted by applicable law, Cypress reserves the right to make changes to this document without further notice. Cypress does not assume any liability arising out of the application or use of any product or circuit described in this document. Any information provided in this document, including any sample design information or programming code, is provided only for reference purposes. It is the responsibility of the user of this document to properly design, program, and test the functionality and safety of any application made of this information and any resulting product. Cypress products are not designed, intended, or authorized for use as critical components in systems designed or intended for the operation of weapons, weapons systems, nuclear installations, life-support devices or systems, other medical devices or systems (including resuscitation equipment and surgical implants), pollution control or hazardous substances management, or other uses where the failure of the device or system could cause personal injury, death, or property damage ("Unintended Uses"). A critical component is any component of a device or system whose failure to perform can be reasonably expected to cause the failure of the device or system, or to affect its safety or effectiveness. Cypress is not liable, in whole or in part, and you shall and hereby do release Cypress from any claim, damage, or other liability arising from or related to all Unintended Uses of Cypress products. You shall indemnify and hold Cypress harmless from and against all claims, costs, damages, and other liabilities, including claims for personal injury or death, arising from or related to any Unintended Uses of Cypress products.

Cypress, the Cypress logo, Spansion, the Spansion logo, and combinations thereof, PSoC, CapSense, EZ-USB, F-RAM, and Traveo are trademarks or registered trademarks of Cypress in the United States and other countries. For a more complete list of Cypress trademarks, visit [cypress.com](http://cypress.com). Other names and brands may be claimed as property of their respective owners.